



# FUKUCOM COMPANY LTD.

## 福靈有限公司

FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,  
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

### SD101A (1N6263)...SD101C

#### SILICON SCHOTTKY BARRIER DIODES for general purpose applications

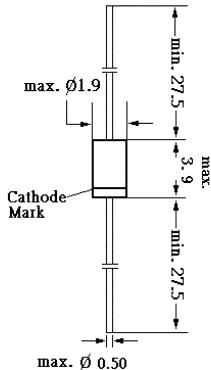
The SD101 Series is a metal on silicon Schottky barrier device which is protected by a PN junction guard ring. The low forward voltage drop and fast switching make it ideal for protection of MOS devices, steering, biasing and coupling diodes for fast switching and low logic level applications.

The SD101A is equivalent to the 1N6263.

This diode is also available in MiniMELF case with type designation LL101A, B, C.

These diodes are delivered taped.

Details see "Taping".



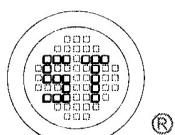
Glass case JEDEC DO-35

Dimensions in mm

#### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RRM}$	60	V
	$V_{RRM}$	50	V
	$V_{RRM}$	40	V
Power Dissipation	$P_{tot}$	400 <sup>1)</sup>	mW
Max. Single Cycle Surge 10 s Square wave	$I_{FSM}$	2	A
Junction Temperature	$T_j$	200	$^\circ\text{C}$
Storage Temperature Range	$T_s$	-55 to +200	$^\circ\text{C}$

<sup>1)</sup> Valid provided the leads direct at the case are kept at ambient temperature.



SEMTECH

Dated : 31/12/2002



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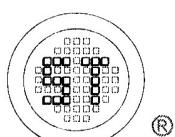
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## **SD101A (1N6263)...SD101C**

**Characteristics at  $T_{amb} = 25^\circ C$**

		Symbol	Min.	Typ.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\mu A$	SD101A	$V_{(BR)R}$	60	-	-	V
	SD101B	$V_{(BR)R}$	50	-	-	V
	SD101C	$V_{(BR)R}$	40	-	-	V
Forward Voltage Drop at $I_F = 1mA$  at $I_F = 15mA$	SD101A	$V_F$	-	-	0.41	V
	SD101B	$V_F$	-	-	0.4	V
	SD101C	$V_F$	-	-	0.39	V
	SD101A	$V_F$	-	-	1	V
	SD101B	$V_F$	-	-	0.95	V
	SD101C	$V_F$	-	-	0.9	V
Leakage Current at $V_R = 50V$ at $V_R = 40V$ at $V_R = 30V$	SD101A	$I_R$	-	-	200	nA
	SD101B	$I_R$	-	-	200	nA
	SD101C	$I_R$	-	-	200	nA
Junction Capacitance at $V_R = 0V$ , $f = 1MHz$	SD101A	$C_{tot}$	-	-	2 <sup>1)</sup>	pF
	SD101B	$C_{tot}$	-	-	2.1	pF
	SD101C	$C_{tot}$	-	-	2.2	pF
Reverse Recovery Time at $I_F = I_R = 5mA$ , recover to 0.1 $I_R$	$t_{rr}$	-	-	1	ns	

<sup>1)</sup> JEDEC limit specification on capacitance for 1N6263 is 2.2 pF



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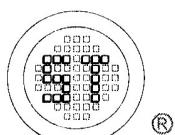
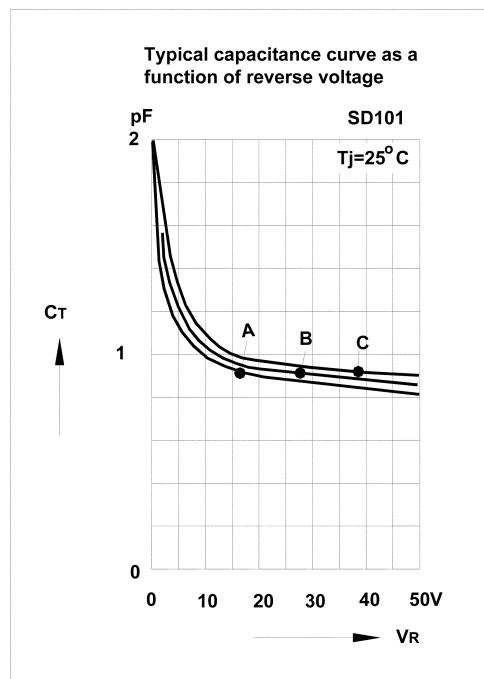
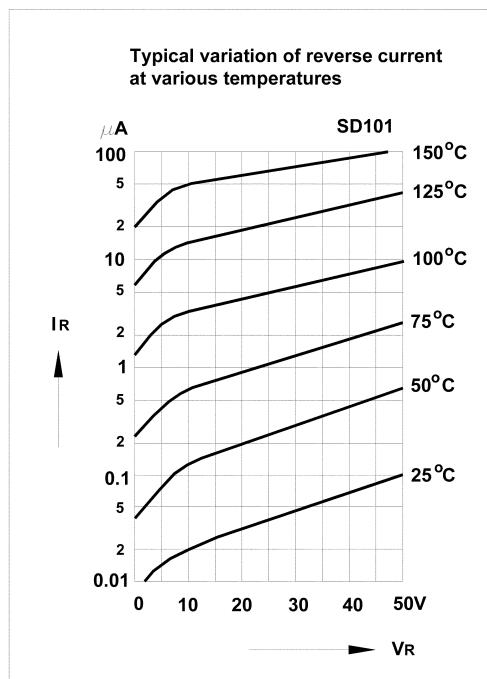
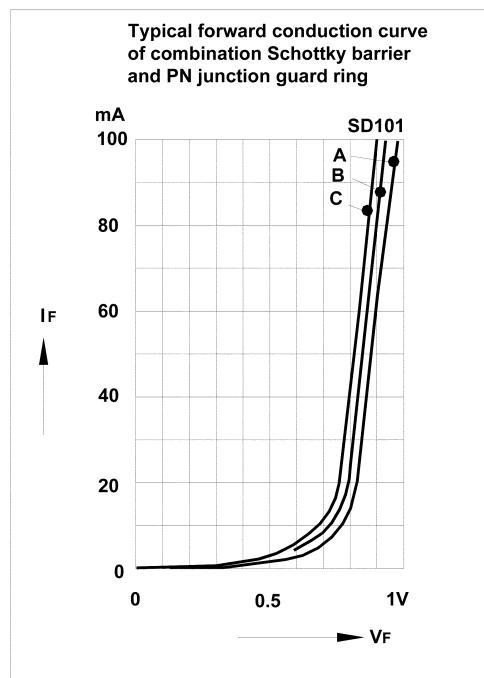
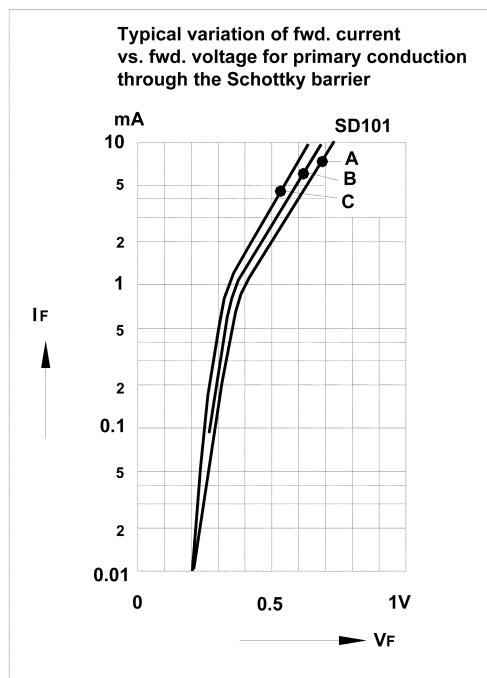
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